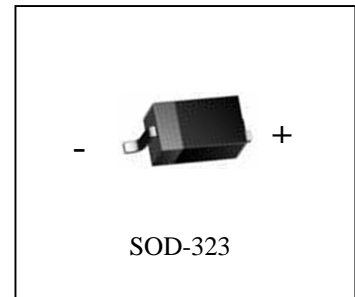


SCHOTTKY BARRIER DIODE

**SD103AWS
SD103BWS
SD103CWS**

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Reverse Capacitance



MARKING: SD103AWS: S4 SD103BWS: S5 SD103CWS: S6

Maximum Ratings and Electrical Characteristics, Single Diode @TA=25 °C

Parameter	Symbol	SD103AWS	SD103BWS	SD103CWS	Unit
Peak Repetitive Peak reverse voltage	VRRM				
Working Peak DC Reverse Voltage	VRWM VR	40	30	20	V
RMS Reverse Voltage	VR(RMS)	28	21	14	V
Forward Continuous Current	IF	350			mA
Repetitive Peak Forward Current,@t 1.0s	IFSM	1.5			A
Power Dissipation	Pd	200			mW
Thermal Resistance Junction to,Ambient	R JA	625			°C/W
Storage temperature	Tstg	-65~+125			°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	SD103AWS SD103BWS SD103CWS	40 30 20			V	IR=10A IR=10A IR=10A
Forward voltage	VF			0.37 0.60	V	IF=20mA IF=200mA
Reverse current	SD103AWS SD103BWS SD103CWS			5.0	µA	VR=3V VR=2V VR=2V
Junction Capacitance	CJ		50		pF	VR=0,f=1MHz
Reverse Recovery Time	trr		10		ns	IR=IF=200mA Irr=0.1*IR,RL=100

SD103AWS
SD103BWS Typical Characteristics
SD103CWS

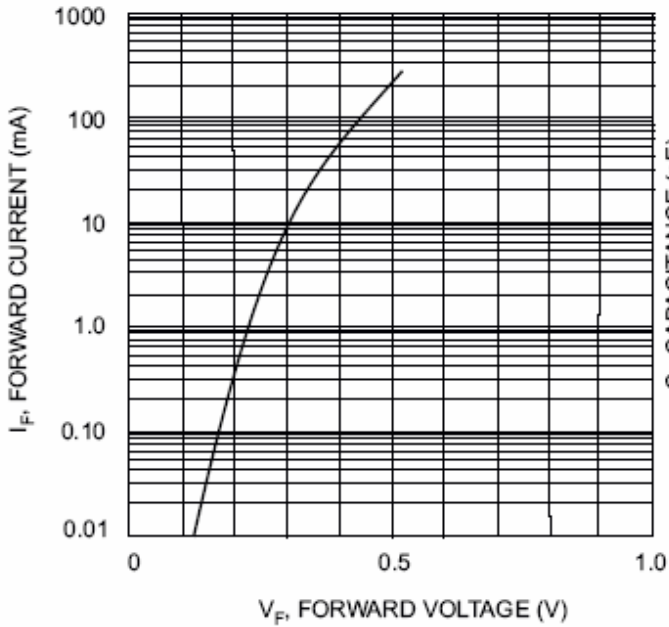


Fig. 1 Typical Forward Characteristics

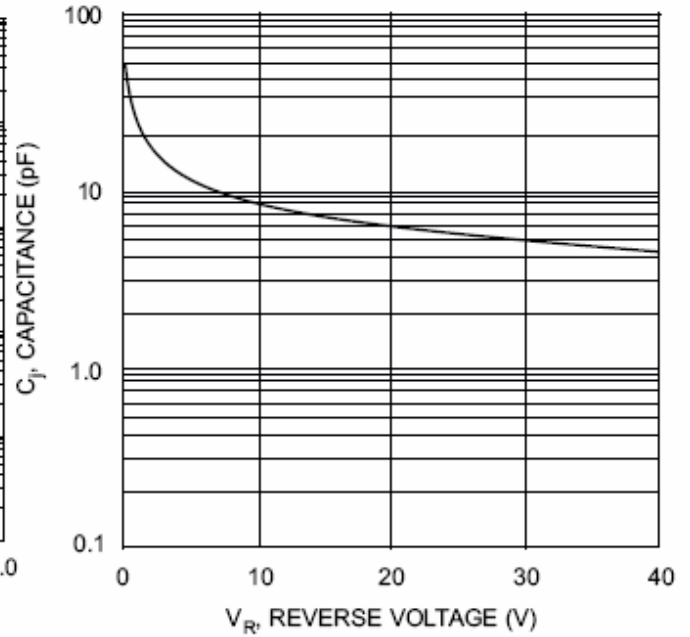


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage